

# 基于 MAPS 的 LHCb 上游径迹探测器升级

## MAPS-based Upstream Tracker for LHCb Upgrade II



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On behalf of the U2UT group

第三届半导体辐射探测器研讨会，合肥，2023年5月12日

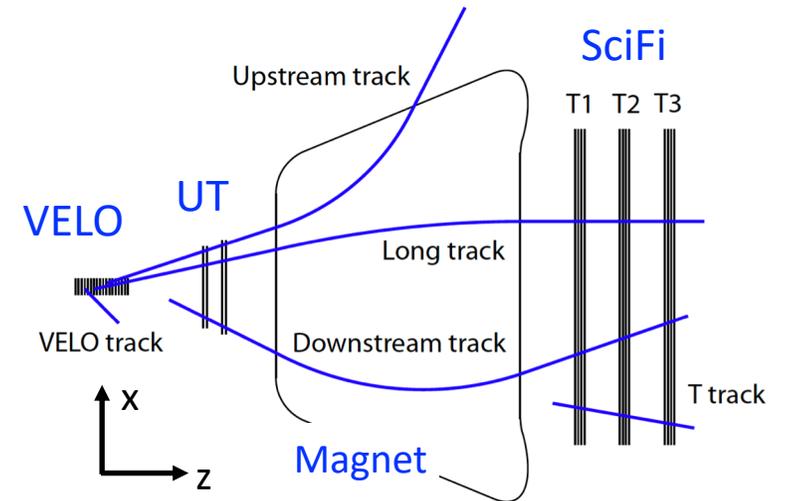
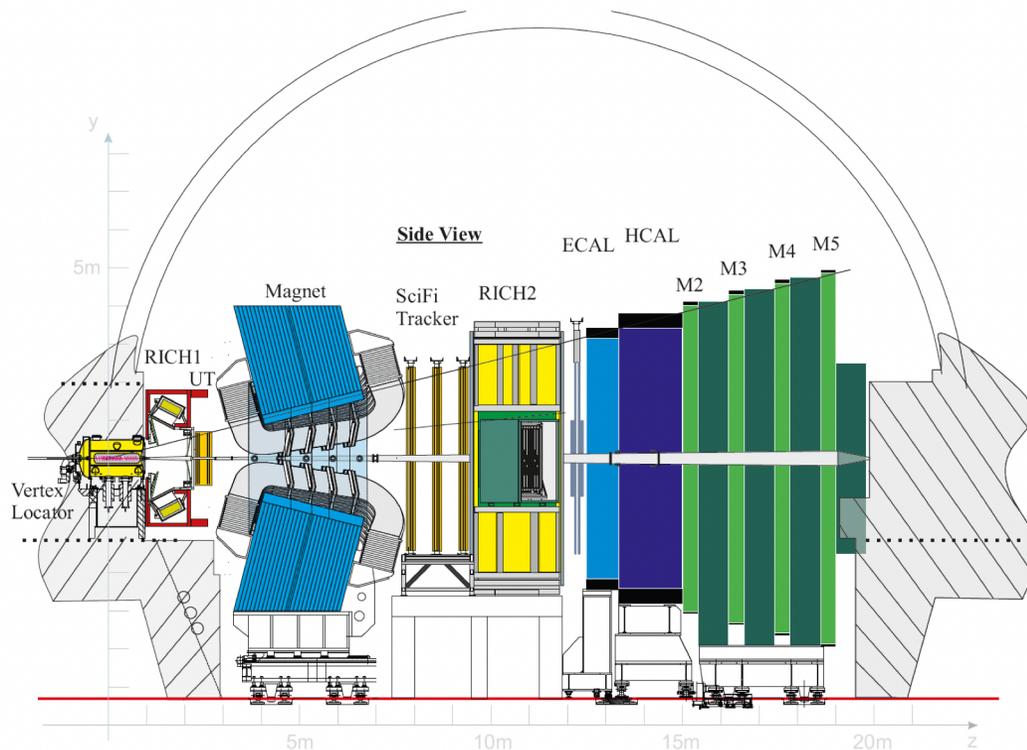
# Content

- Introduction to Upstream Tracker
- LHCb Upgrade II challenges for UT
- MAPS-based UT for Upgrade II
  - System design
  - Sensor options: HVCMOS vs. Small-electrode CMOS
  - Simulation and optimization
- Summary



# Tracking in LHCb Upgrade I

- LHCb: single-armed spectrometer dedicated to heavy flavour study at LHC
- Upgrade I completed in March 2023
  - Luminosity increase  $\times 5 \rightarrow 2 \times 10^{33} \text{cm}^{-2} \text{s}^{-1}$
  - Removal of Hardware trigger

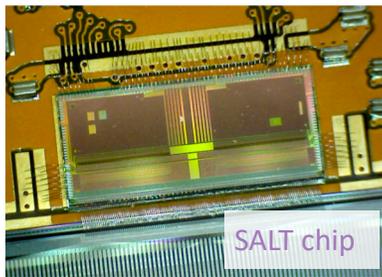


- New sub-detectors for the tracking system
- **Upstream Tracker (UT)** is essential:
  - Speed-up of VELO-SciFi matching
  - Reduction of ghost rate
  - Reconstruction of long-lived particles

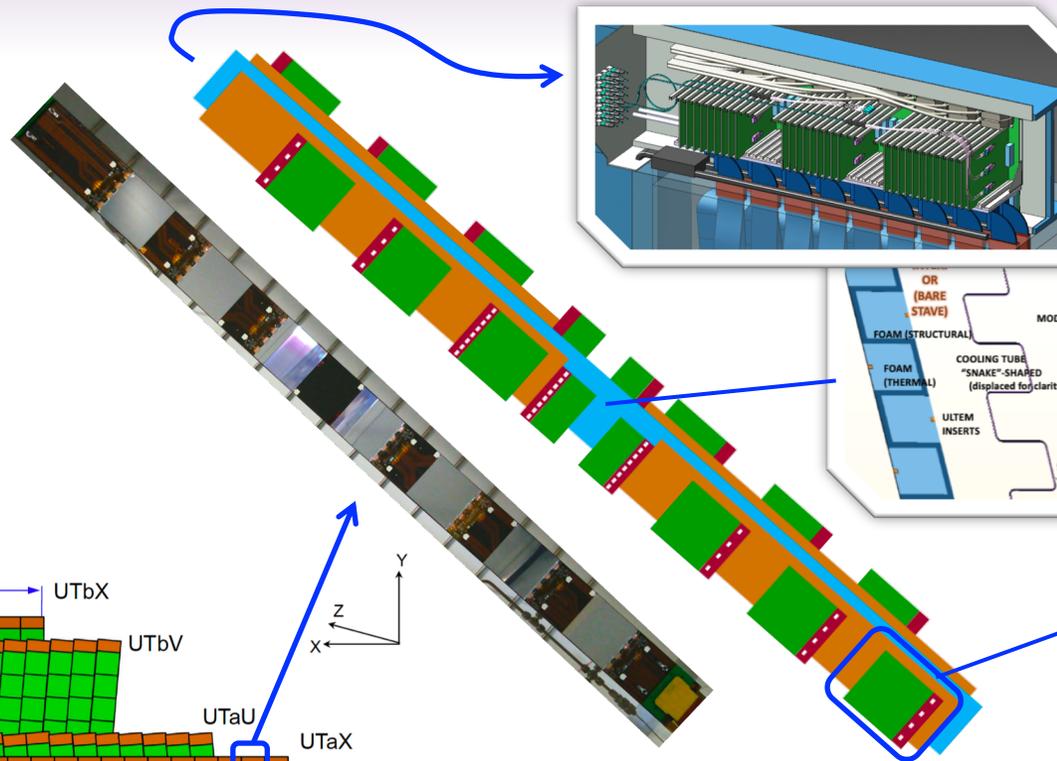
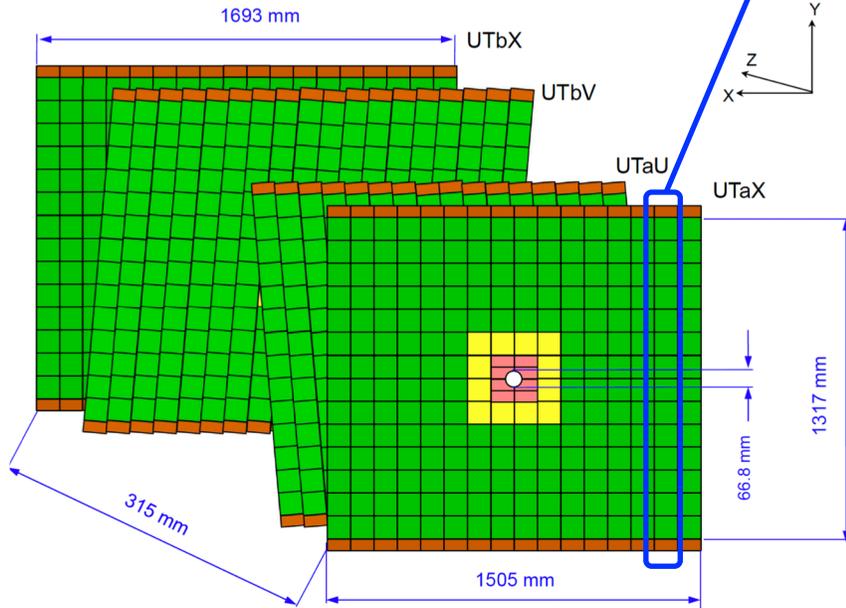


# Upstream Tracker (UT)

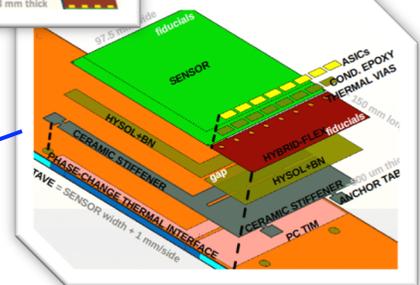
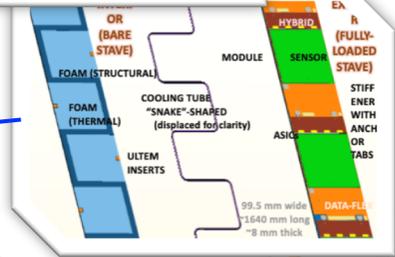
- Four planes of silicon strip detectors
  - Strips along y-axis (or  $\pm 5^\circ$ )
- Higher segmentation near the center
- Readout ASICs: SALT at sensor proximity



Sensor	A	B	C	D
Type	p-in-n	n-in-p	n-in-p	n-in-p
Thickness( $\mu\text{m}$ )	320	250	250	250
Pitch ( $\mu\text{m}$ )	187.5	93.5	93.5	93.5
Length (mm)	~100	~100	~50	~50
Strips/sensor	512	1024	1024	1024
SALTs/sensor	4	8	8	8
Numbers	888	48	16	16



Peripheral Electronics Processing Interface



- Modules mounted on both sides of staves to allow overlapping
- Stave: Cooling tube (CO<sub>2</sub>) embedded in foam core + CFRP face sheets
- Stave readout at both ends:
  - data formatting, timing distribution, control and optical conversion

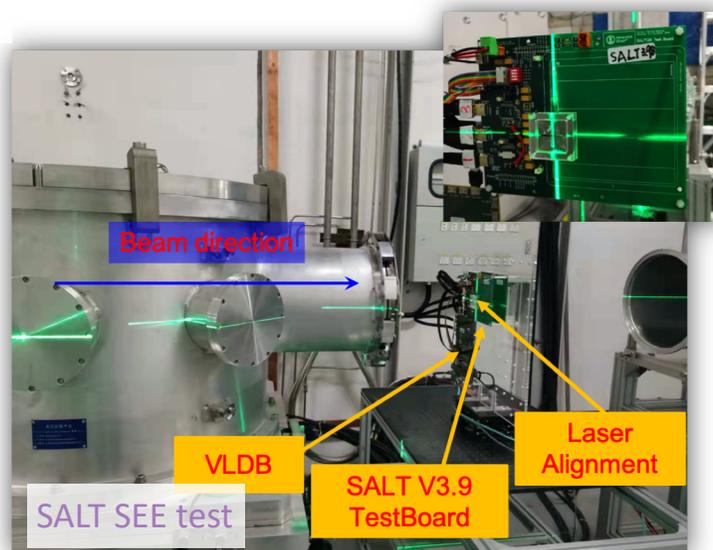
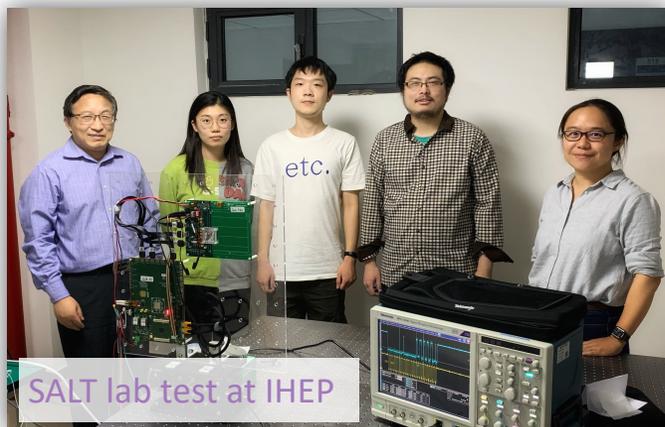


# Chinese contribution



- Chinese groups play a key role
- Study of SEE effects in SALT chips using domestic and oversea facilities
  - CSNS, CIAE
- Integration and installation at CERN

Supported by NSFC project 11961141015  
“LHCb升级中径迹探测器和数据获取系统的研究”



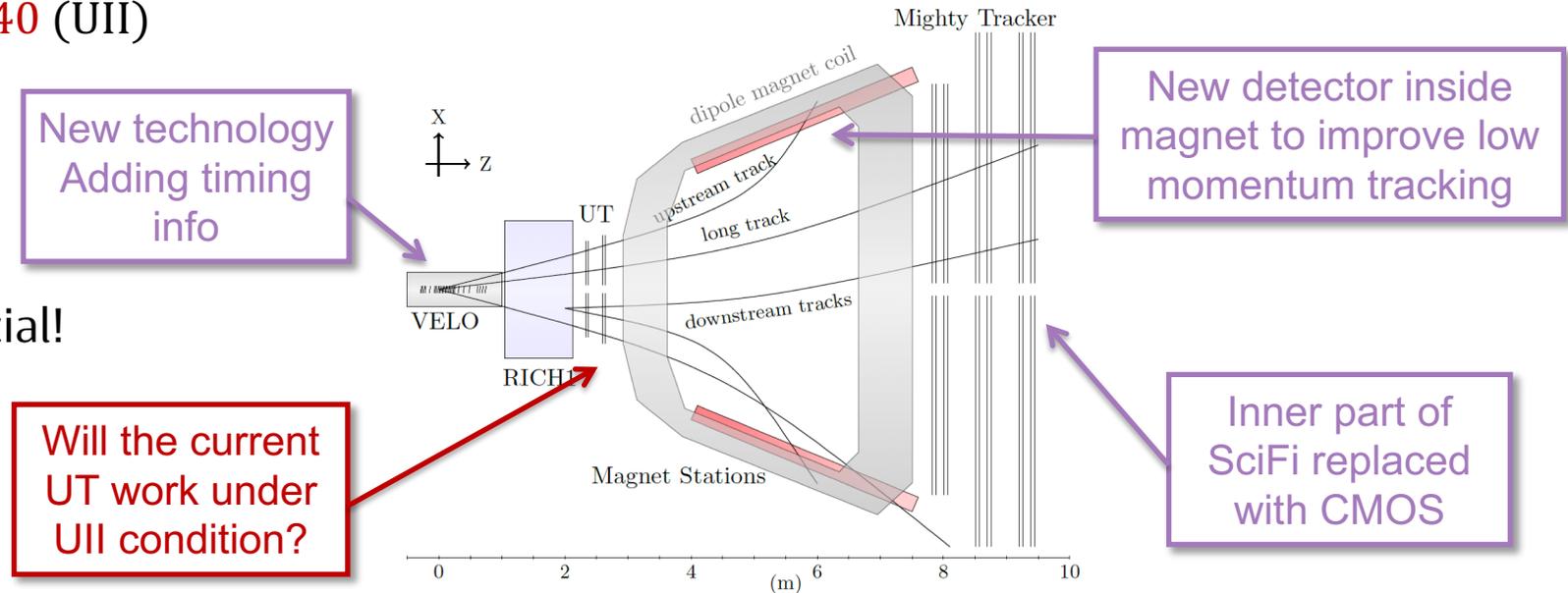
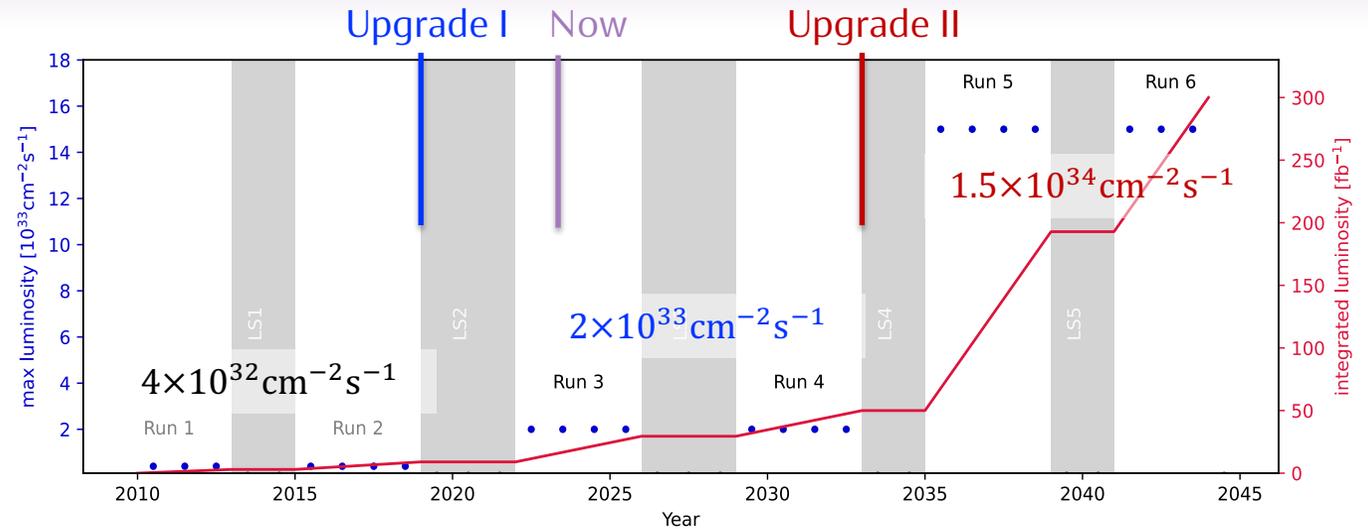
# LHCb Upgrade II

- Upgrade II planned at LS4 to fully exploit the HL-LHC potential in flavor physics & beyond
- Aim for an luminosity of  $1.5 \times 10^{34} \text{ cm}^{-2} \text{ s}^{-1}$  and  $\mathcal{L}_{\text{int}} \sim 300 \text{ fb}^{-1}$  in the lifetime of LHC

## High-lumi operation challenges:

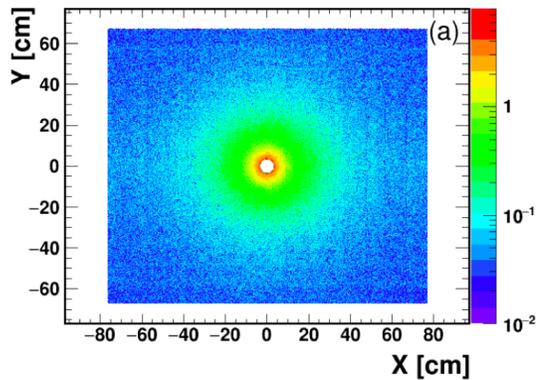
- Large pile-up:  $\mu \sim 1 \rightarrow 5$  (UI)  $\rightarrow 40$  (UII)
- High multiplicity ( $\rightarrow$  occupancy)
- Severe radiation damage

## Efficient tracking in real-time is crucial!

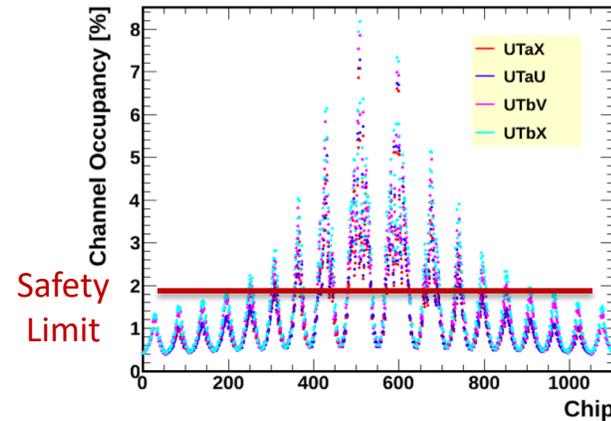
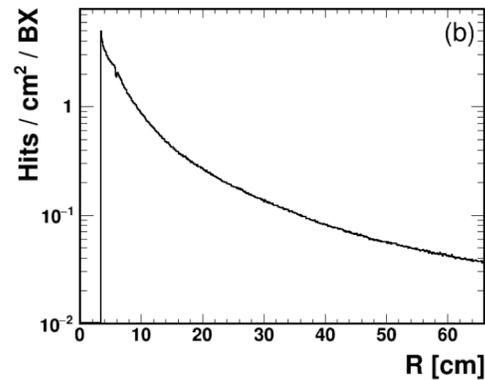


# Challenges for UT in Upgrade II

- Simulation performed with UT in UII condition
  - Max hit density  $\sim 6 \text{ hits/cm}^2/\text{BX}$  for beam-beam crossings in pp
  - For Pb-Pb  $\sim 3 \text{ hits/cm}^2/\text{BX}$ , but multiplicity is higher
- Current UT cannot work safely after  $\times 7.5$  increase in luminosity!
  - Max occupancy  $\sim 10\%$
  - Data rate much more than current UT can handle
  - Max fluence of  $\sim 3 \times 10^{15} n_{\text{eq}}/\text{cm}^2$  may be too high for current sensor



Hit density in a layer under UII condition



Channel occupancy

3	3	3	3	3	3	3	3	3
3	3	3	3	3	3	3	4	4
3	3	3	3	3	4	4	4	4
3	3	3	4	4	4	4	5	5
3	3	3	4	4	4	5	7	7
4	4	4	4	4	6	7	7	9
4	4	4	4	5	6	9	12	14
								19

Required links / ASIC  
Max 5 available!

Beam center



# MAPS-based UT upgrade

- Proposal for a new UT using CMOS MAPS technology
  - Higher granularity for high multiplicity
  - Better radiation tolerance
- R&D collaboration (U2UT) formed mainly by Chinese and French institutes
  - New members welcome in or outside LHCb!

LHCb Upgrade II TDR, CERN-LHCC-2021-012;  
 Y. Li, Nucl. Inst. Meth. A 1032 (2022) 166629



### 3.3 Upstream Tracker

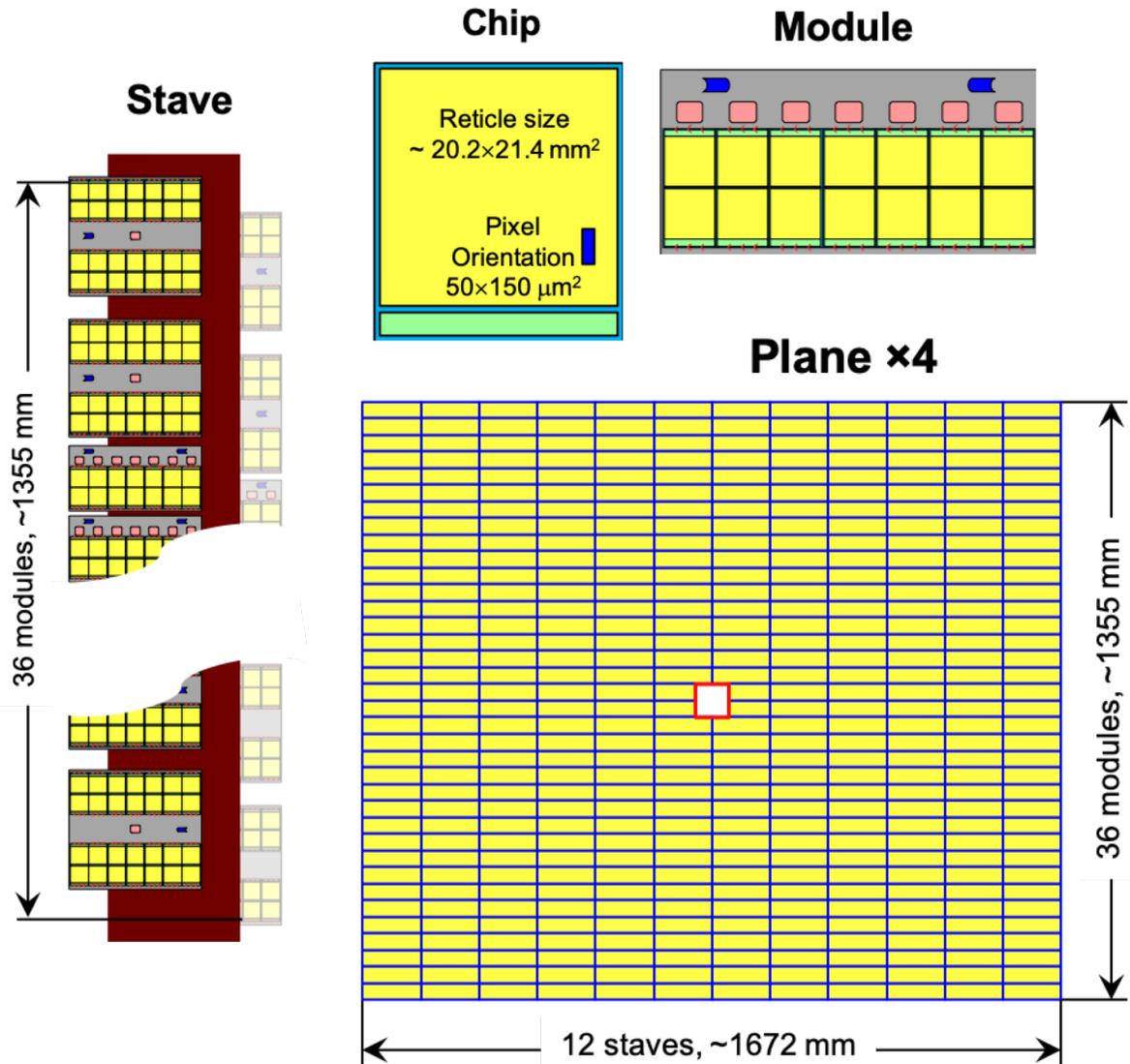
The UT detector is located just upstream of the magnet and covers the full detector acceptance [19]. The detector facilitates the track matching between the segments near the primary vertex in the VELO and downstream of the magnet in the MT; without the UT the rate of fake matches would be unacceptably high. Furthermore, it improves the momentum resolution for tracks traversing the full spectrometer and, since it sits in the fringe field of the magnet, provides a first fast momentum estimate for the trigger. It also doubles the acceptance of the spectrometer for the reconstruction of long-lived particle decays such as  $K_S^0 \rightarrow \pi^+\pi^-$  or  $\Lambda \rightarrow p\pi^-$ , many of which decay after the VELO, by combining the UT and the downstream tracker information. Finally, allows to reconstruct slow pions from, for example  $D^*$  decays.

The Upgrade I UT [19] consists of four planes of silicon strip sensors. The emphasis is on precision reconstruction in the bend-plane of the magnet (xz) and this leads to a requirement of a strip pitch of around  $100\ \mu\text{m}$ . Stereo-angles of  $\pm 5^\circ$  allow 3D reconstruction with modest y resolution. The system was optimized for a luminosity of  $\mathcal{L} = 2 \times 10^{33}\ \text{cm}^{-2}\text{s}^{-1}$ , and can operate at 1.5 times higher luminosity. However, it cannot cope with the data rate expected in Upgrade II, where the peak luminosity will be a factor of 7.5 higher. Moreover, the high occupancy (up to  $\sim 10\%$ ) would significantly compromise the UT performance. Finally, the innermost silicon sensors are not qualified to sustain a radiation dose beyond that expected from  $50\ \text{fb}^{-1}$  of integrated luminosity. For Upgrade II the expected radiation dose for the inner part of the detector is  $3 \times 10^{15}\ \text{neq}/\text{cm}^2$ . A new UT detector is mandatory to fulfil the challenging experimental conditions of the HL-LHC expected for Run 5 and beyond.

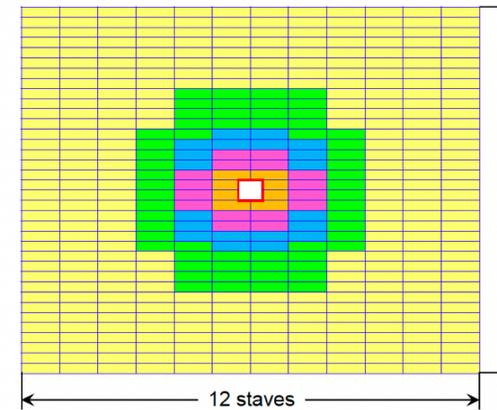
In the following sections the proposed design for the upgraded UT detector is discussed using CMOS MAPs technology and give results from preliminary performance studies, together with an R&D plan and associated cost.



# System design



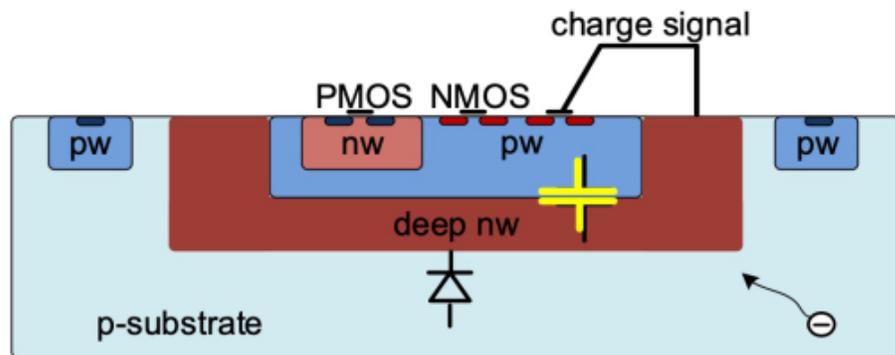
- Preliminary system design proposed
- Certain features of current UT kept
  - Stave structure
  - Strip/ long-pixel orientation
- Drawing for HV-CMOS technology, similar for small-electrode CMOS



Ring	5	4	3	2	1
e-links / chip	1	1	1	1-3	2-7
Gbps / e-link	0.32	0.64	1.28	1.28	1.28
IpGBT / module	0.5	1	2	7	14/10
Num of modules	1312	240	80	64	32
Num of IpGBTs	656	240	160	448	384

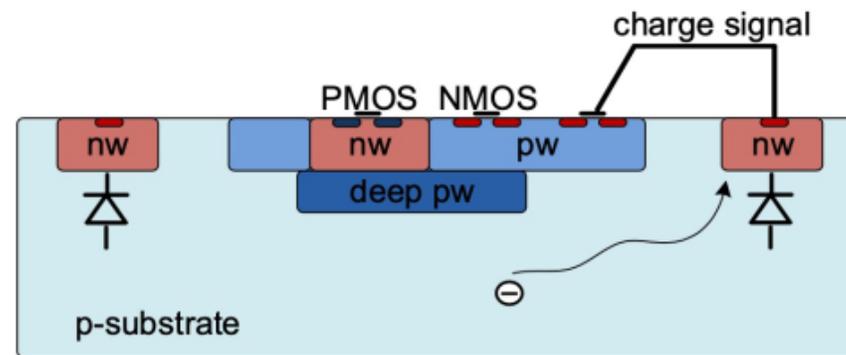


# Main sensor options



## High Voltage CMOS

- Circuitry inside the charge collection well
- Large uniform electric field
- On average shorter drift path
- **Better radiation hardness** (less trapping)
- HV-CMOS process **commercially available**
- Large sensor capacitance (pw and dnw)
- Foundries: TSI-180, Lfoundry-150



## CMOS with small electrode

- Circuitry outside the charge collection well
- Optimization of little low-field regions
- On average longer drift path
- Radiation hardness needs process modifications
- **Very small sensor capacitance**
- Foundries: Towerjazz-180, TPSCo-65...



# Sensor specifications

Characteristics	LV-CMOS	HV-CMOS
Chip size	$3.5 \times 3.5 \text{ cm}^2$	$2.0 \times 2.0 \text{ cm}^2$
Pixel size	$30 \times 30 \text{ um}^2$	$50 \times 150 \text{ um}^2$
Chip thickness	~ 100 um	
Position resolution	5-10 um	15, 40 um
Time resolution	O (1) ns	
Power consumption	100 – 300 mW/cm <sup>2</sup>	
Radiation dose	$3 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$ , or 240 MRad TID	
Data rate per chip	Up to 30 Gb/s	Up to 9 Gb/s

Capable of distinguishing 25ns bunch crossing

Depends on timing resolution

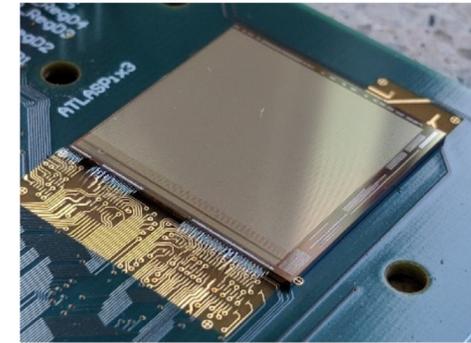
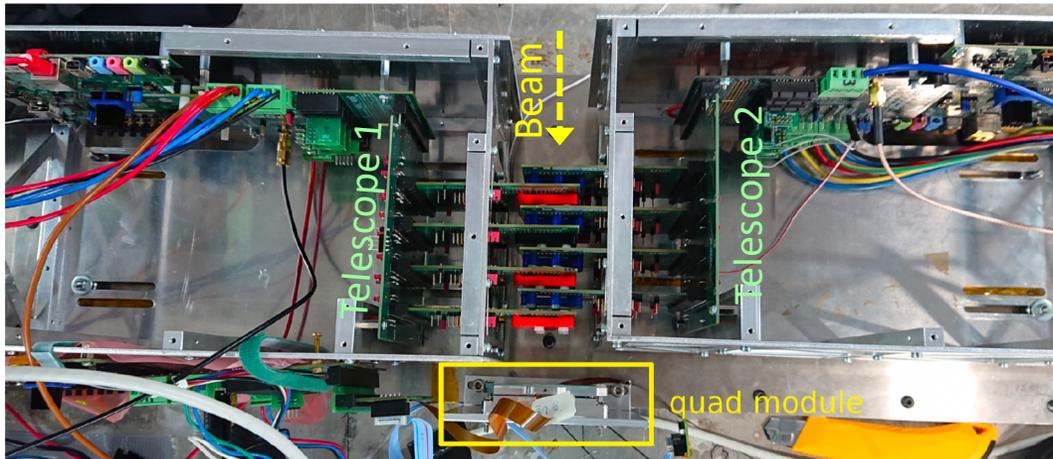
Affects cooling requirements

Achievable by HV-CMOS



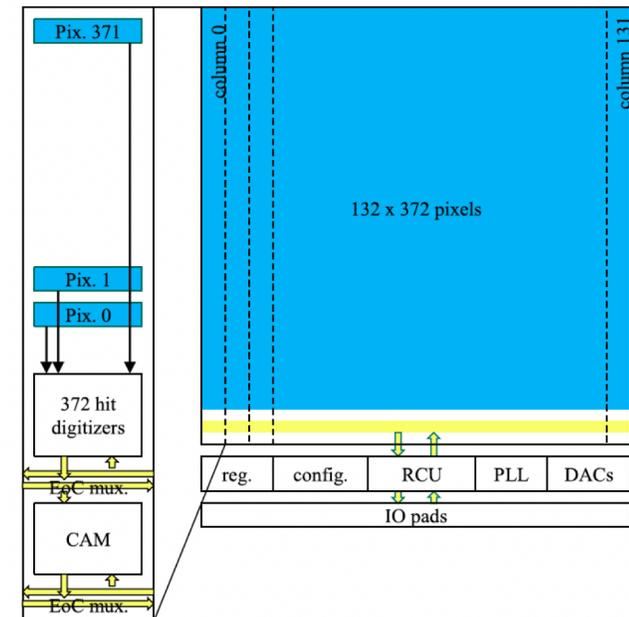
# HVCMOS option: ATLASPix3

- ATLASPix3 chip developed for HL-LHC
  - TSI 180nm HV process on 200  $\Omega$ cm substrate
  - Pixel size  $50 \times 150 \mu\text{m}^2$
  - 132 columns  $\times$  372 rows ( $20.2 \times 21 \text{ mm}^2$  chip)
  - Time resolution:  $\sim 7$  (4) ns w/o (with) ToT correction
  - Functioning after  $\sim 10^{15} n_{\text{eq}}/\text{cm}^2$
  - Power consumption  $\sim 160 \text{ mW}/\text{cm}^2$
- Also serves as potential candidate for CEPC tracker, performance studied in testbeam (Apr 2022)



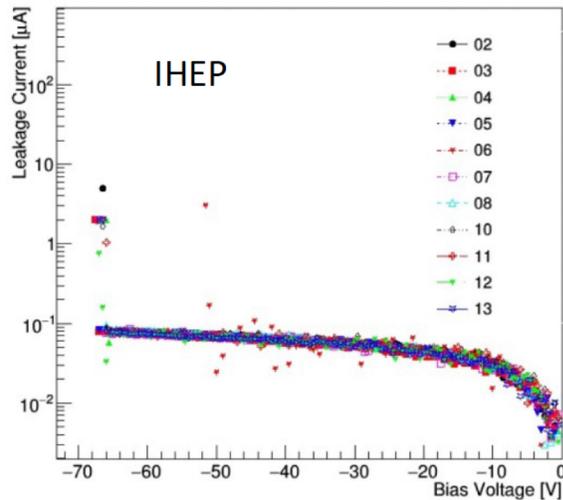
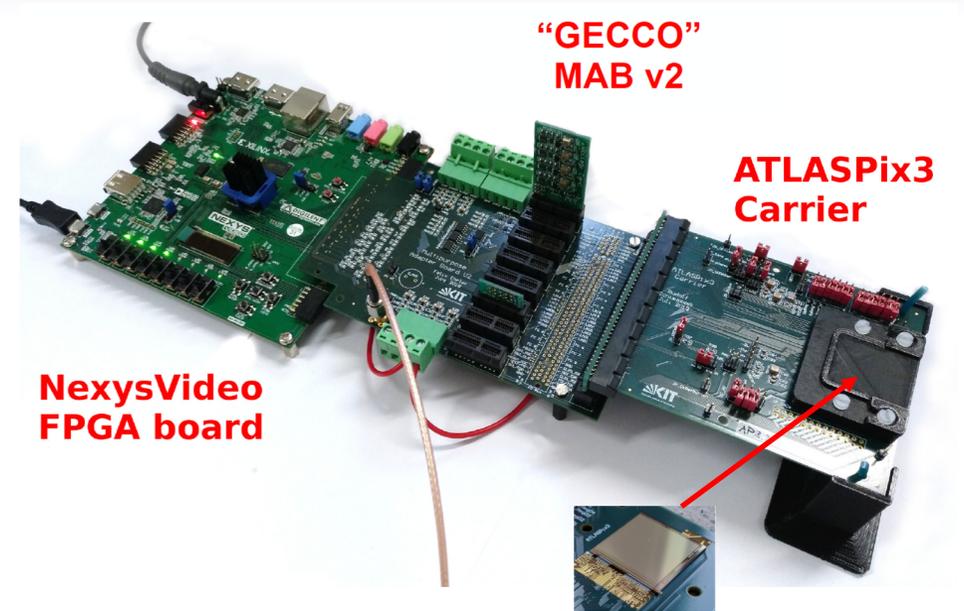
I. Peric et al., *IEEE JSSC*, Vol 56, No.8, Aug. 2021

徐子骏 “CEPC silicon tracker”

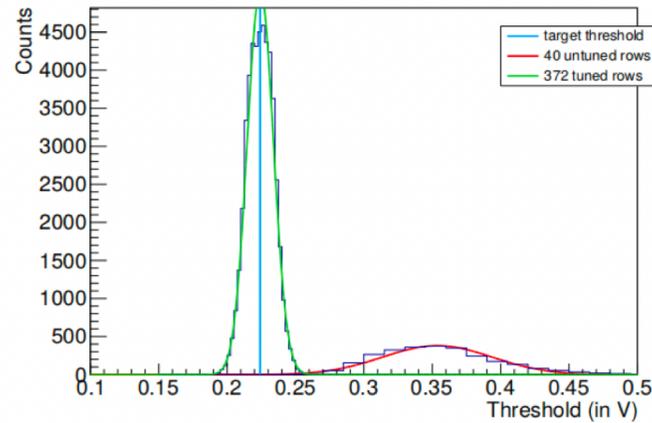


# Test with ATLASPix3

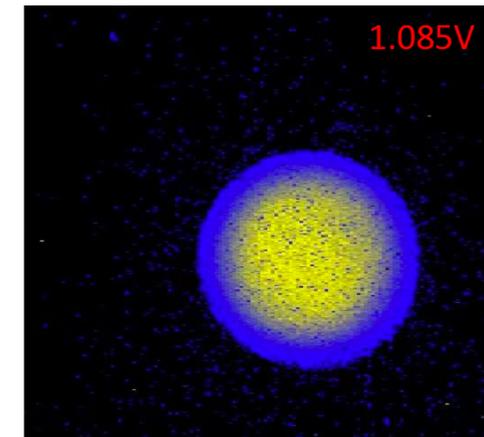
- The ATLASPix3.1 chips had been extensively tested at IHEP, readout using a GECCO system.
- Threshold trimming and noise performance, noise  $\sim 60$  e for threshold  $\sim 1700$  e.
- Tested in cosmic ray and various radioactive sources.



IV measurement



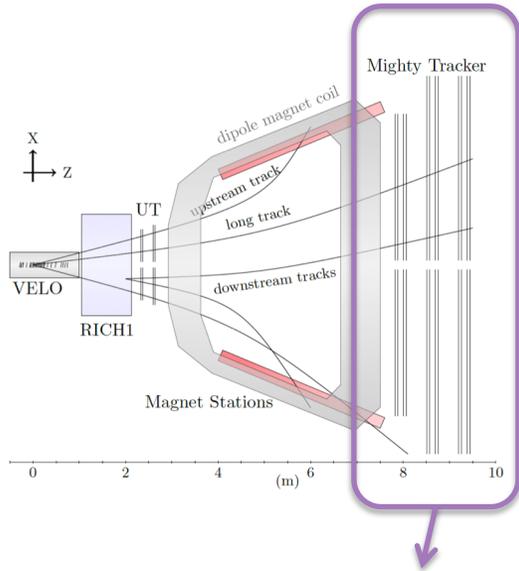
Threshold trimming



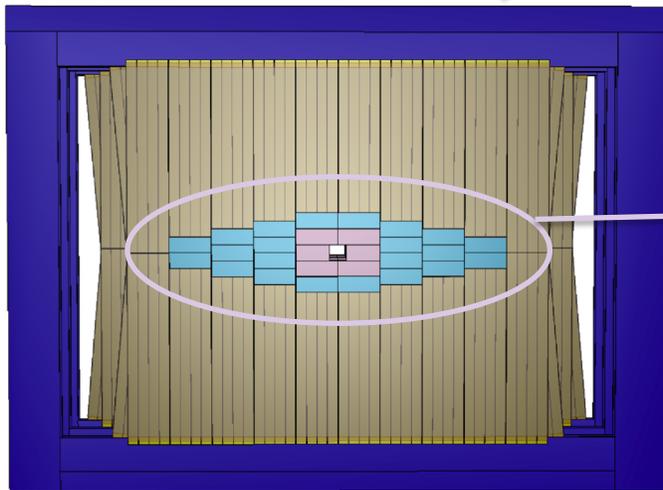
Hitmap with Fe55 source



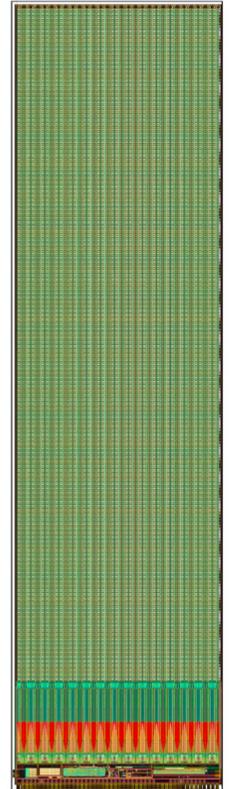
# Synergy with Mighty Tracker



- Innermost region of SciFi will be replaced by CMOS tracker
- Less radiation; more complex integration and more pressing timeline
- R&D based on HV-CMOS
  - Tests with ATLASPix3
  - Dedicated MightyPix1 on TSI 180nm received recently
- Synergy with UT under discussion



<b>Pixel size</b>	< 100 $\mu\text{m}$ x 300 $\mu\text{m}$
<b>In-time efficiency</b>	> 99% within 25 ns window
<b>Timing resolution</b>	$\sim$ 3 ns within 25 ns window
<b>Radiation tolerance</b>	$6 \times 10^{14}$ 1 MeV $n_{\text{eq}}/\text{cm}^2$
<b>Power consumption</b>	< 150 mW/cm <sup>2</sup>
<b>Data transmission</b>	4 links of 1.28 Gb/s each
Compatibility with the LHCb readout system	



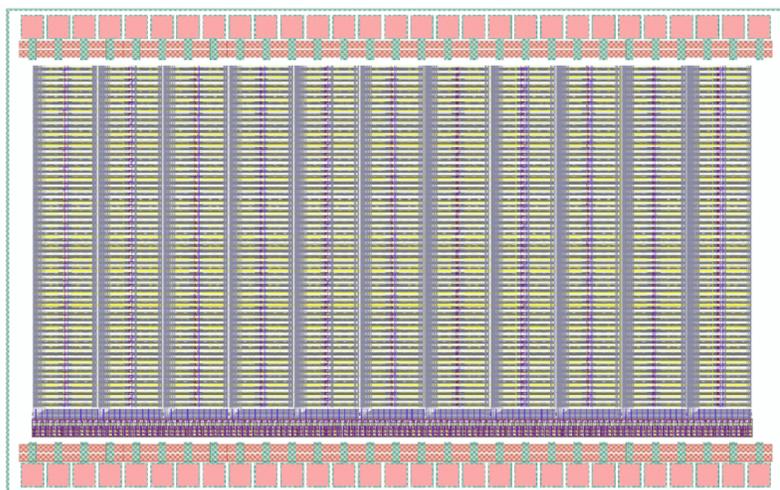
MightyPix1 floorplan  
1/4 of a full matrix size



# Attempts for alternative foundries

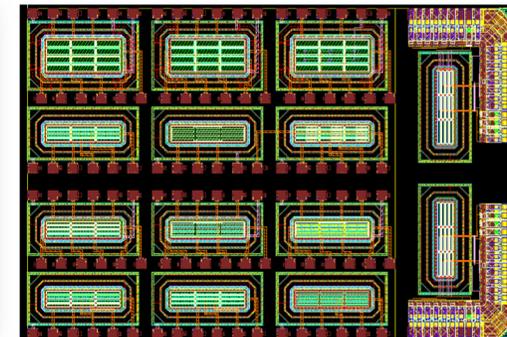
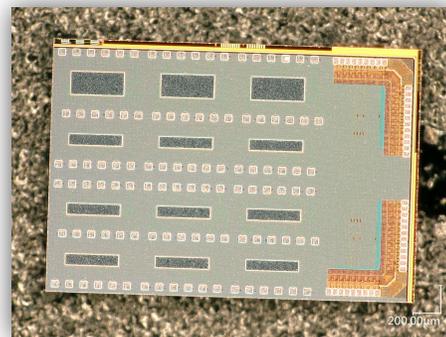
## HLMC 55nm HV process

- Pixel array being designed by KIT and IHEP, pixel size  $25 \times 150 \mu\text{m}^2$
- Caveat: wafer with high-resistance substrate not yet supported.
- Still seeking MPW opportunity



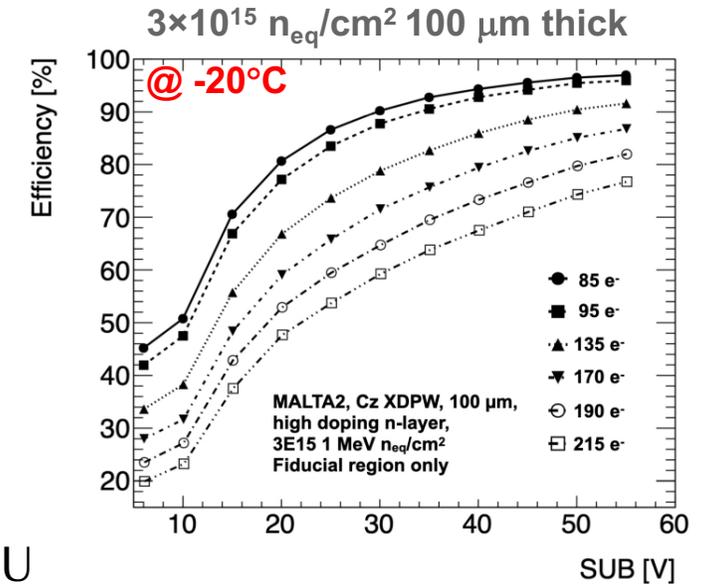
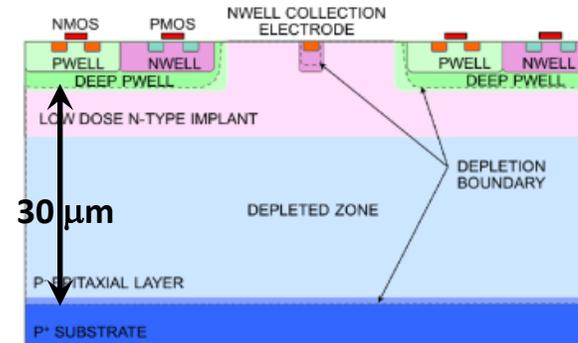
## SMIC 55nm process

- HV and normal (Low-Leakage) process available
- Possible to use high-resistance wafer  $1\text{k} / 2\text{k} \Omega\text{m}$
- A MPW submission in Oct 2022 with LL process:
  - Variety of passive sensor diodes and amplifiers
- Seeking MPW opportunity in 2023 with HV process



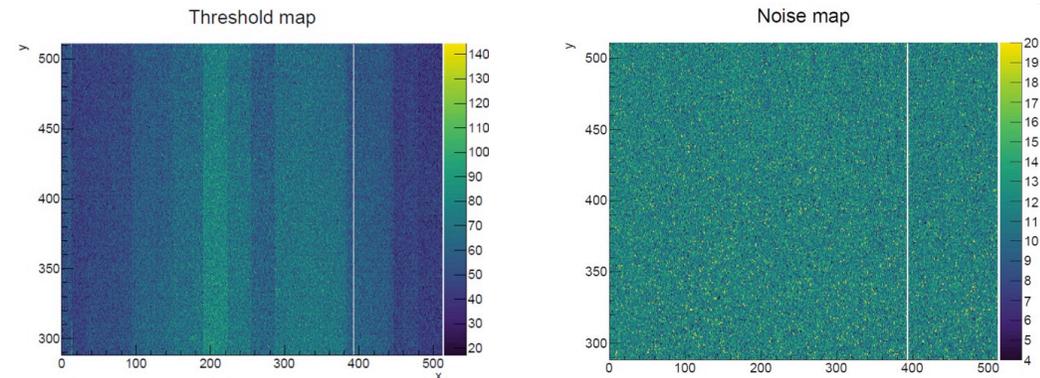
# Small electrode CMOS: TowerJazz MALTA2

- TowerJazz 180 nm CMOS modified process designed by CERN, Bonn U. and CPPM
  - Low dose n-type implant ensures uniform depletion of high resistivity epitaxial layer
  - Active region : 25 - 30  $\mu\text{m}$
  - Available total thickness : 50 - 100 - 300  $\mu\text{m}$
  - Bias voltages: 6 - 20 V (substrate), 6V (pwell)



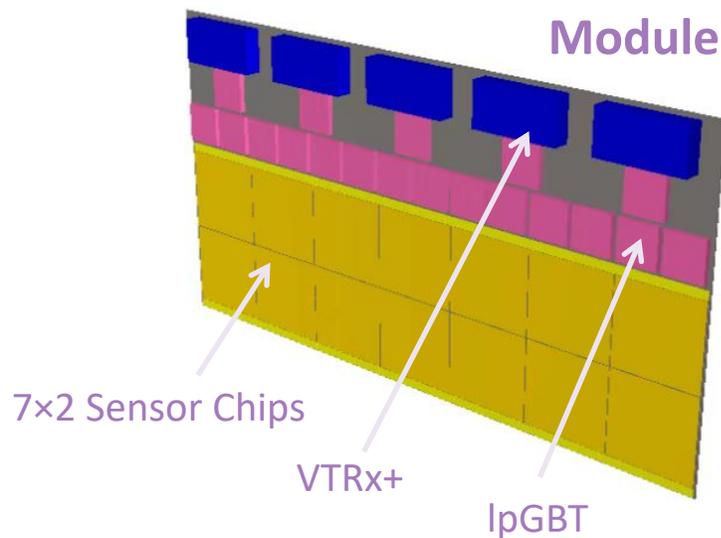
## ■ MALTA2 tested at CEA-IRFU

- Using Kintex-7 dev board for control & readout
- Common threshold set to  $\sim 60$  e  $\Rightarrow$  dispersion  $\sim 13.7$  e.
- Average noise  $\sim 12$  e as expected, homogenous over the matrix.

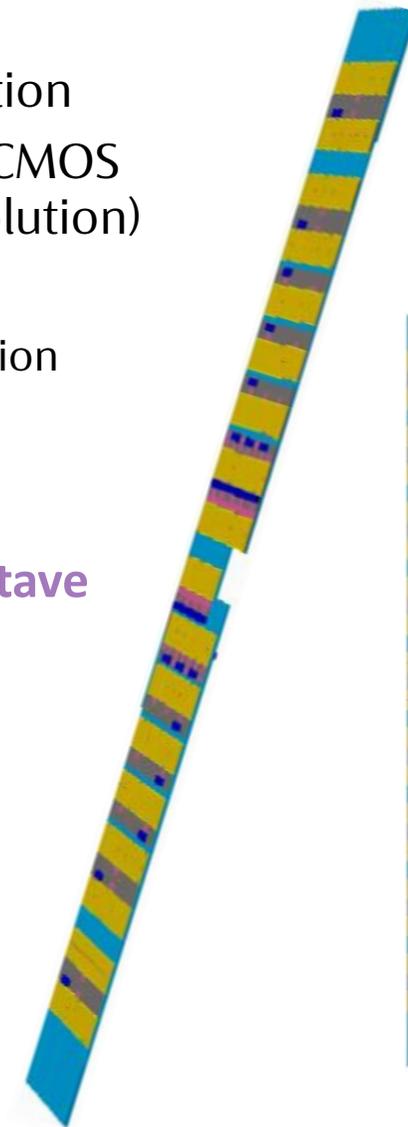


# Detector modelling in software

- Full simulation mandatory for design optimization
- Detector description has been created for HV-CMOS solution (easily adaptable to small electrode solution)
- Created in both [DDDB](#) and [DD4HEP](#) format
  - Integration into LHCb simulation and reconstruction software framework ongoing

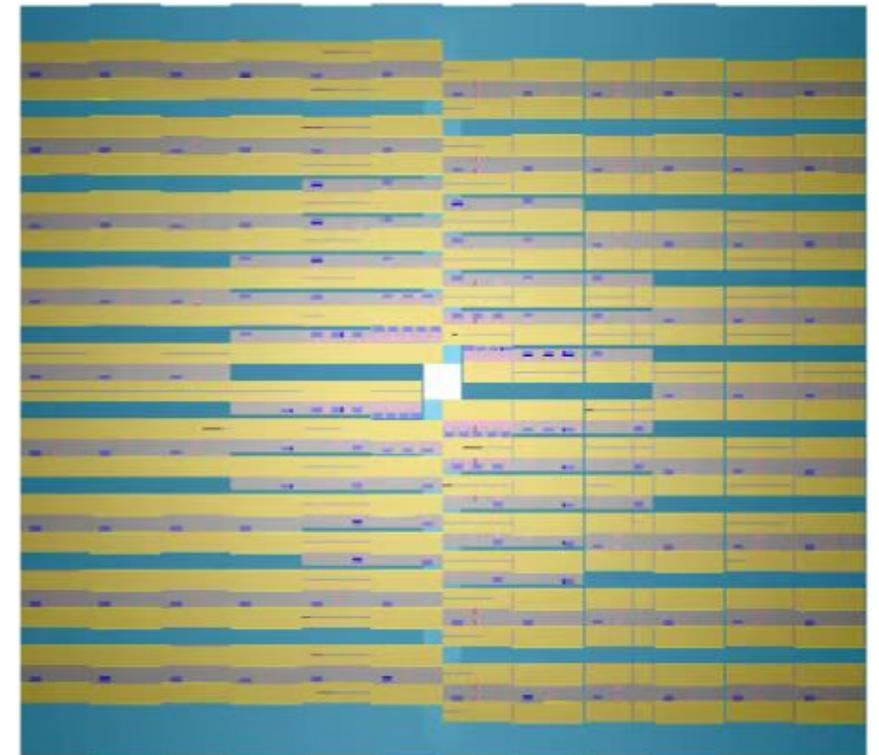


Stave



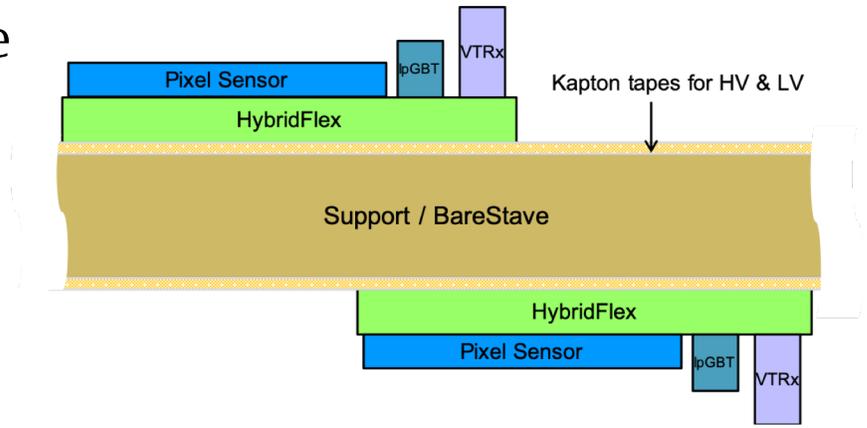
Plane

(4 planes are identical for now)

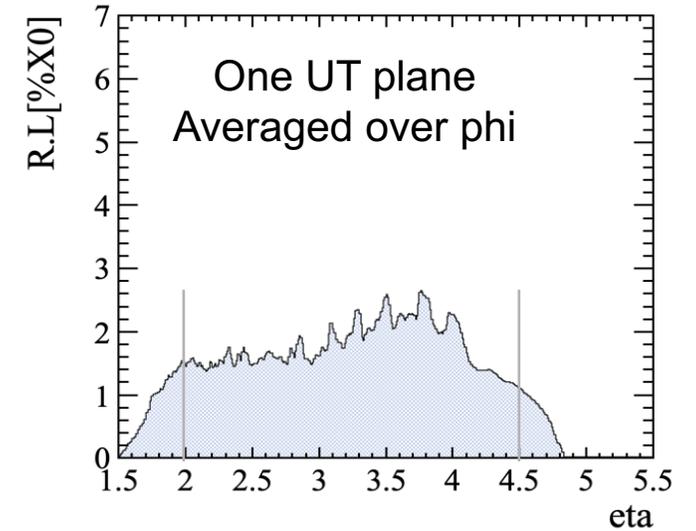
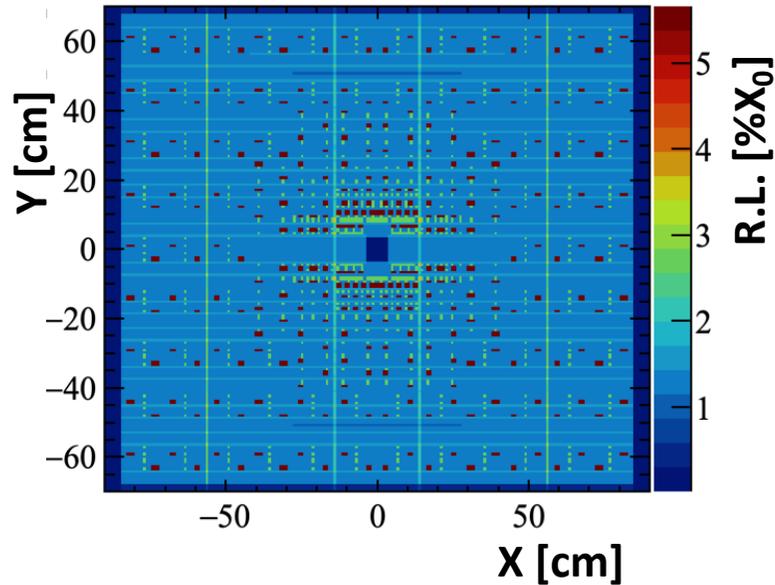


# Material scan

- Material scan performed with a simplified stave structure
  - Detailed composite of VTRx+ and lpGBT not known
  - Not all electronics components included
  - Yet a good starting point for material budget study

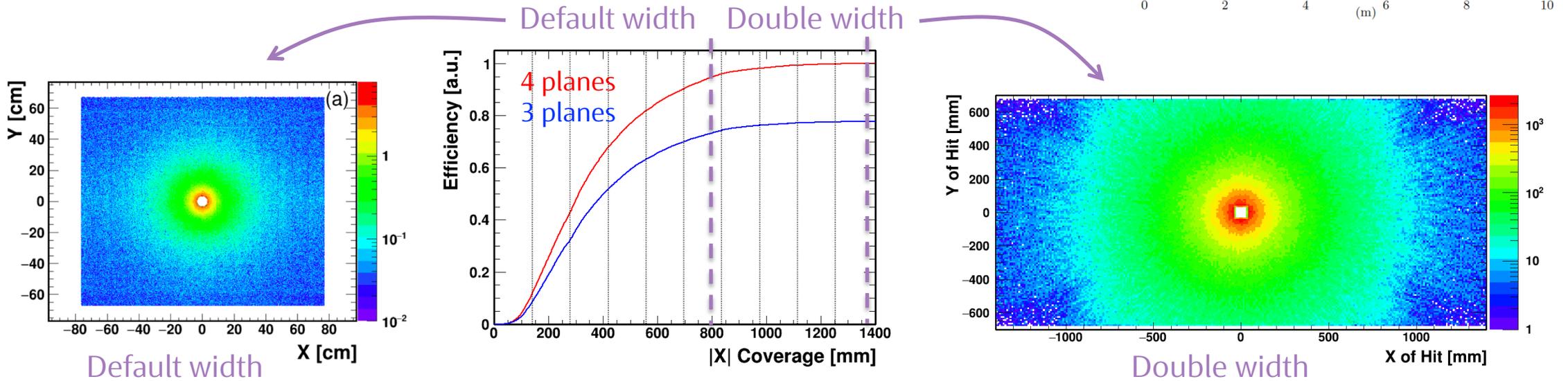
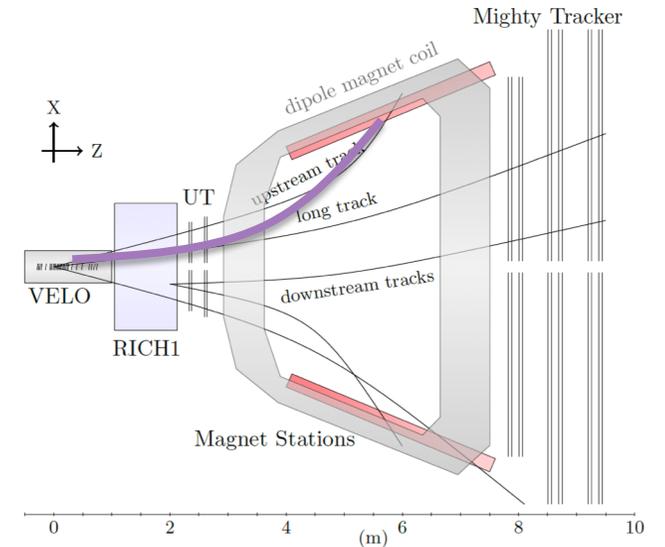


(Preliminary)	Thickness [mm]	RL ( $2 < h < 4.5$ ) [% $X_0$ ]
Pixel Sensor	0.200	0.24
lpGBT	1.250	0.25
VTRx+	4.000	0.27
HybridFlex	0.300	0.42
Kapton Tape	0.100	0.14
BareStave	4.000	0.21
<b>One plane</b>	-	<b>1.54</b>



# Detector Optimisation

- Detailed studies foreseen to define / to optimise the UT design
  - Impact on tracking performance of VELO-UT(-MS)
  - Detector acceptance optimization associated with magnet station
  - Optimisation on number and layout of layers (3 vs. 4)
  - Estimation of material budget and cooling options
  - Effect of a possible additional timing layer with different technology
  - ...



# Summary

- LHCb UT has been successfully installed and being commissioned
- For Upgrade II a new UT is compulsory, R&D for a MAPS-based U2UT is ongoing aiming for TDR ~2027
  - HV-CMOS and small-electrode CMOS options
  - Full simulation and optimization studies kicked off
- Chinese groups contributed to UT and leading the MAPS-based UT development
- Your participation and interests are welcome!

Thank you for your time!

Contact: [liyiming@ihep.ac.cn](mailto:liyiming@ihep.ac.cn)

